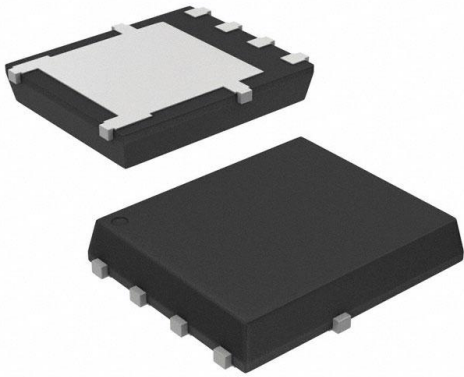


NVMFS5885NLT1G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

| | |
|------------------------------|--|
| DiGi Electronics Part Number | NVMFS5885NLT1G-DG |
| Manufacturer | onsemi |
| Manufacturer Product Number | NVMFS5885NLT1G |
| Description | MOSFET N-CH 60V 10.2A 5DFN |
| Detailed Description | N-Channel 60 V 10.2A (Ta) 3.7W (Ta), 54W (Tc) Surface Mount 5-DFN (5x6) (8-SOFL) |



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NVMFS5885NLT1G

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.5V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Qualification:

AEC-Q101

Supplier Device Package:

5-DFN (5x6) (8-SOFL)

Base Product Number:

NVMFS5885

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

10.2A (Ta)

Rds On (Max) @ Id, Vgs:

15mOhm @ 15A, 10V

Gate Charge (Qg) (Max) @ Vgs:

21 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1340 pF @ 25 V

Power Dissipation (Max):

3.7W (Ta), 54W (Tc)

Grade:

Automotive

Mounting Type:

Surface Mount

Package / Case:

8-PowerTDFN, 5 Leads

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

NVMFS5885NL

MOSFET – Power, Single N-Channel

60 V, 15 mΩ, 39 A

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVMFS5885NLWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit | |
|---|--|------------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 60 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3) | Steady State | $T_{mb} = 25^\circ\text{C}$ | I_D 39 | A |
| | | $T_{mb} = 100^\circ\text{C}$ | 28 | |
| Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3) | Steady State | $T_{mb} = 25^\circ\text{C}$ | P_D 54 | W |
| | | $T_{mb} = 100^\circ\text{C}$ | 27 | |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 3) | Steady State | $T_A = 25^\circ\text{C}$ | I_D 10.2 | A |
| | | $T_A = 100^\circ\text{C}$ | 7.2 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1 & 3) | Steady State | $T_A = 25^\circ\text{C}$ | P_D 3.7 | W |
| | | $T_A = 100^\circ\text{C}$ | 1.8 | |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | I_{DM} 179 | A | |
| Operating Junction and Storage Temperature | T_J, T_{stg} | -55 to 175 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 46 | A | |
| Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{L(pk)} = 18 \text{ A}, L = 0.3 \text{ mH}, R_G = 25 \Omega$) | E_{AS} | 49 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|--|-----------------|-------|--------------------|
| Junction-to-Mounting Board (top) – Steady State (Notes 2, 3) | $R_{\Psi J-mb}$ | 2.8 | $^\circ\text{C/W}$ |
| Junction-to-Ambient – Steady State (Note 3) | $R_{\theta JA}$ | 41 | |

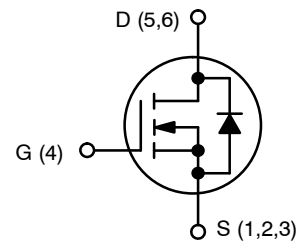
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51-12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.



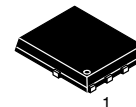
ON Semiconductor®

<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 60 V | 15 mΩ @ 10 V | 39 A |
| | 21 mΩ @ 4.5 V | |

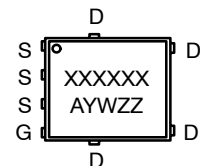


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



- A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS5885NL**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------------------------------|---------------|---|---------------------------|-----|-----------|---------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-to-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 60 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$ | $T_J = 25^\circ\text{C}$ | | 1.0 | μA |
| | | | $T_J = 125^\circ\text{C}$ | | 10 | |
| Gate-to-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |

ON CHARACTERISTICS (Note 4)

| | | | | | | |
|-------------------------------|--------------|--|-----|------|-----|------------|
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$ | 1.5 | | 2.5 | V |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | | 11.6 | 15 | m Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$ | | 15.2 | 21 | |

CHARGES AND CAPACITANCES

| | | | | | | |
|------------------------------|--------------|--|--|------|--|----|
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$ | | 1340 | | pF |
| Output Capacitance | C_{oss} | | | 125 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 85 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 48\text{ V}, I_D = 15\text{ A}$ | | 12 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | 1.1 | | |
| Gate-to-Source Charge | Q_{GS} | | | 4.0 | | |
| Gate-to-Drain Charge | Q_{GD} | | | 6.3 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 48\text{ V}, I_D = 15\text{ A}$ | | 21 | | nC |

SWITCHING CHARACTERISTICS (Note 5)

| | | | | | | |
|---------------------|--------------|---|--|----|--|----|
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 48\text{ V}, I_D = 15\text{ A}, R_G = 2.5\ \Omega$ | | 10 | | ns |
| Rise Time | t_r | | | 64 | | |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | | 18 | | |
| Fall Time | t_f | | | 52 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|----------|--|---------------------------|-----|-----|-----|----|
| Forward Diode Voltage | V_{SD} | $V_{GS} = 0\text{ V}, I_S = 15\text{ A}$ | $T_J = 25^\circ\text{C}$ | | 0.8 | 1.2 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.7 | | |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0\text{ V}, di/dt = 100\text{ A}/\mu\text{s}, I_S = 15\text{ A}$ | | 20 | | ns | |
| Charge Time | t_a | | | 15 | | | |
| Discharge Time | t_b | | | 5.0 | | | |
| Reverse Recovery Charge | Q_{RR} | | | 16 | | | nC |

4. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

NVMFS5885NL

TYPICAL CHARACTERISTICS

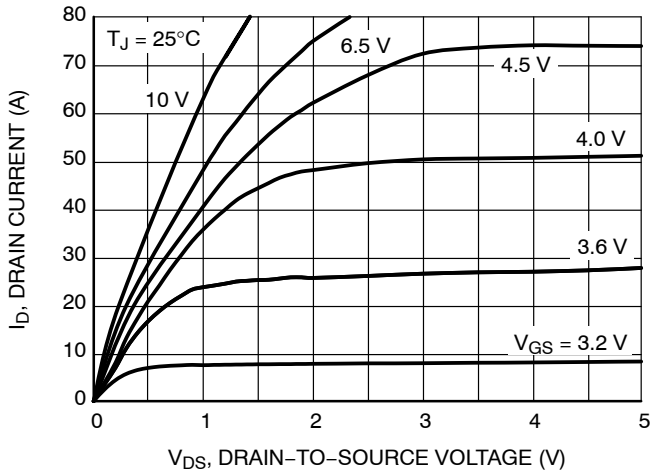


Figure 1. On-Region Characteristics

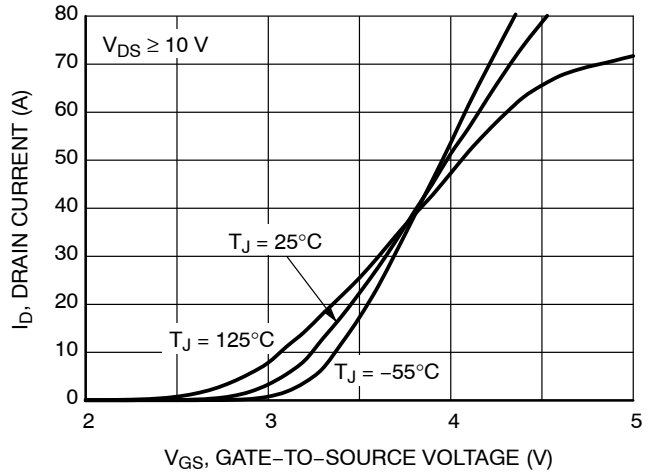


Figure 2. Transfer Characteristics

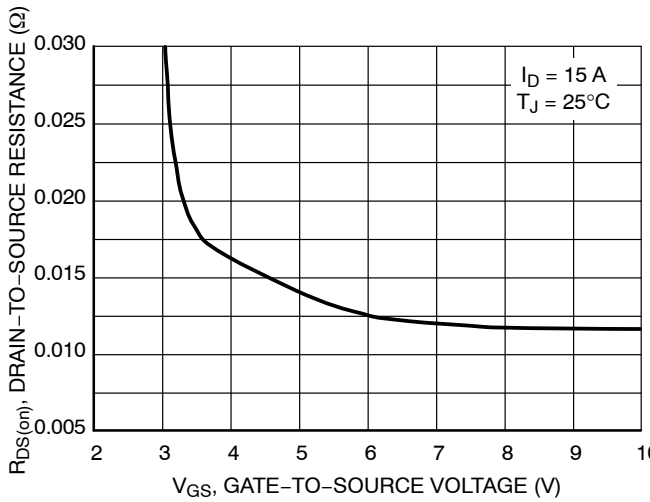


Figure 3. On-Resistance vs. Gate-to-Source Voltage

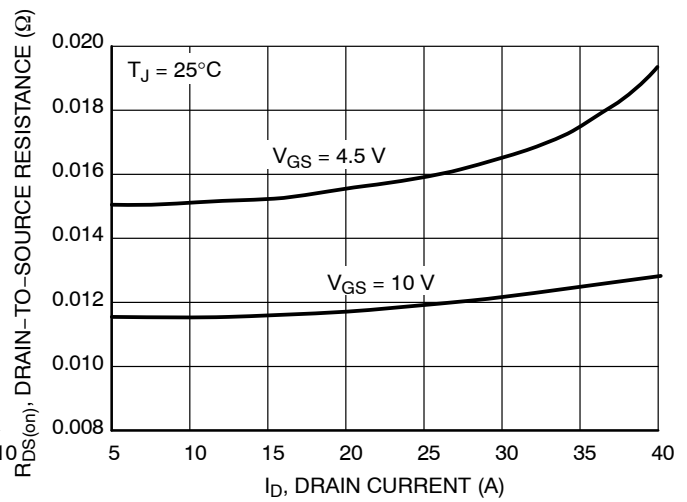


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

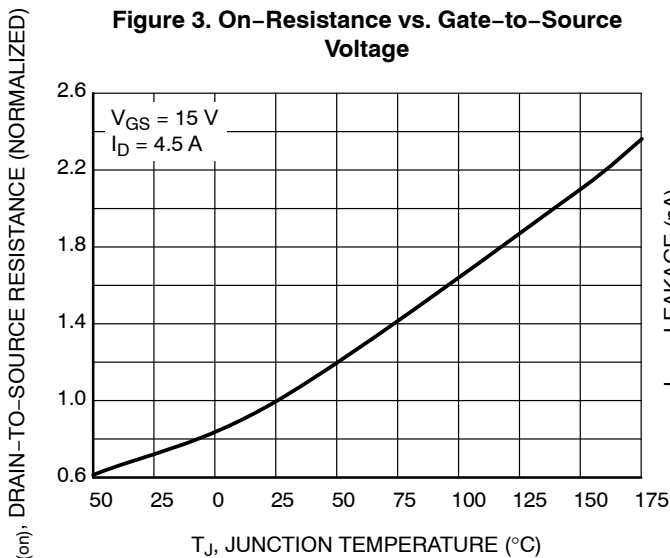


Figure 5. On-Resistance Variation with Temperature

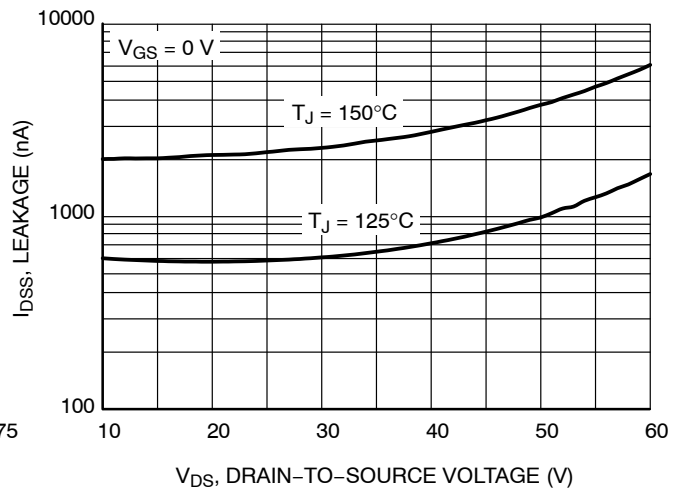


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVMFS5885NL

TYPICAL CHARACTERISTICS

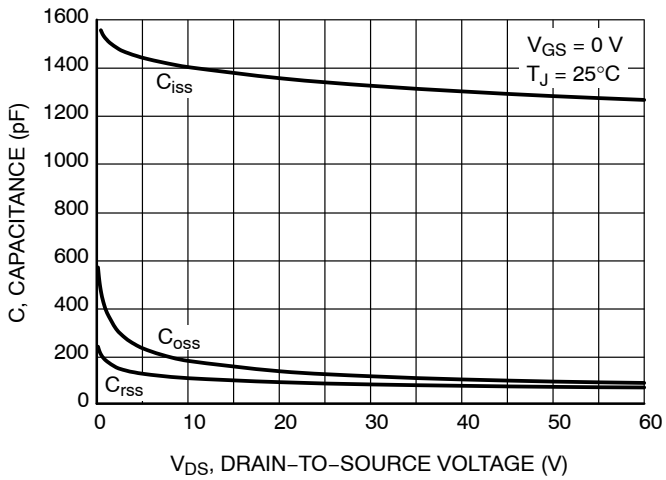


Figure 7. Capacitance Variation

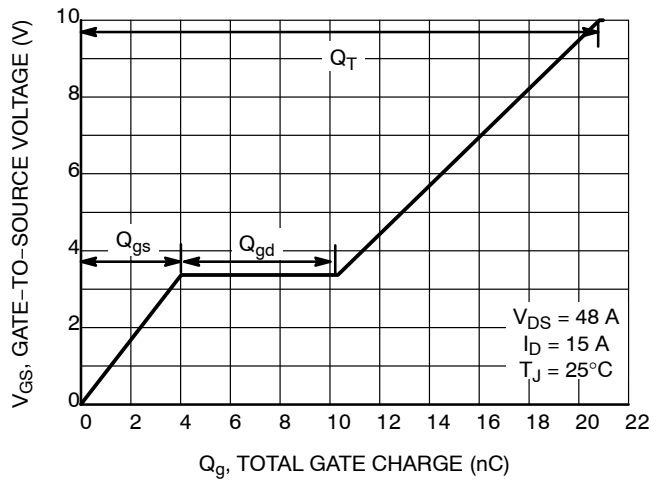


Figure 8. Gate-to-Source Voltage vs. Total Charge

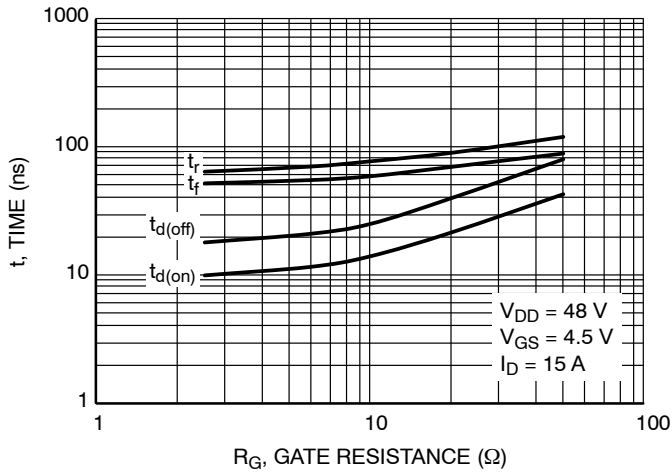


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

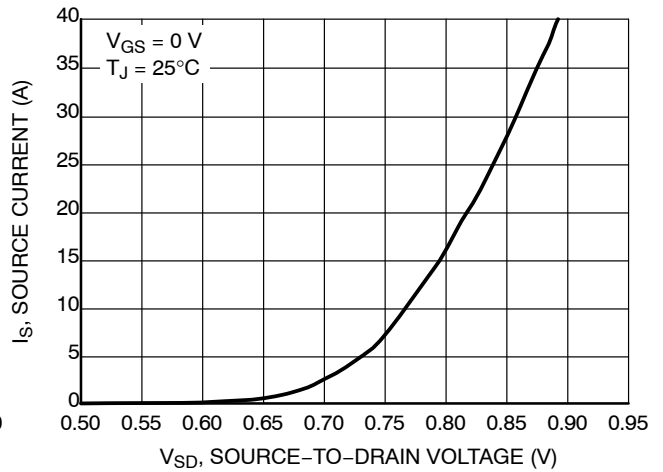


Figure 10. Diode Forward Voltage vs. Current

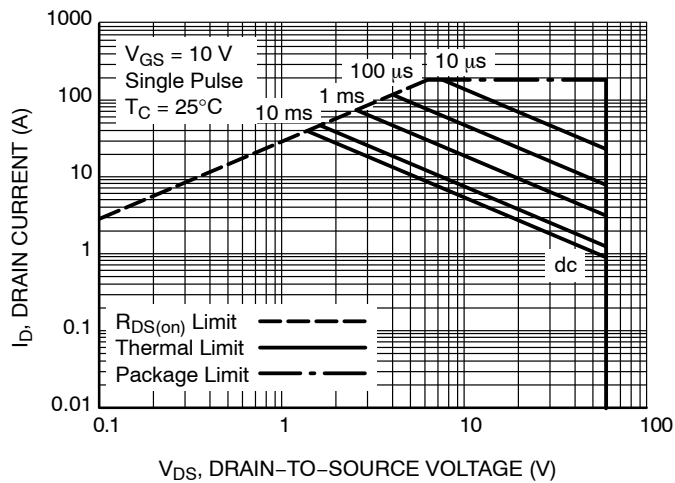


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NVMFS5885NL

TYPICAL CHARACTERISTICS

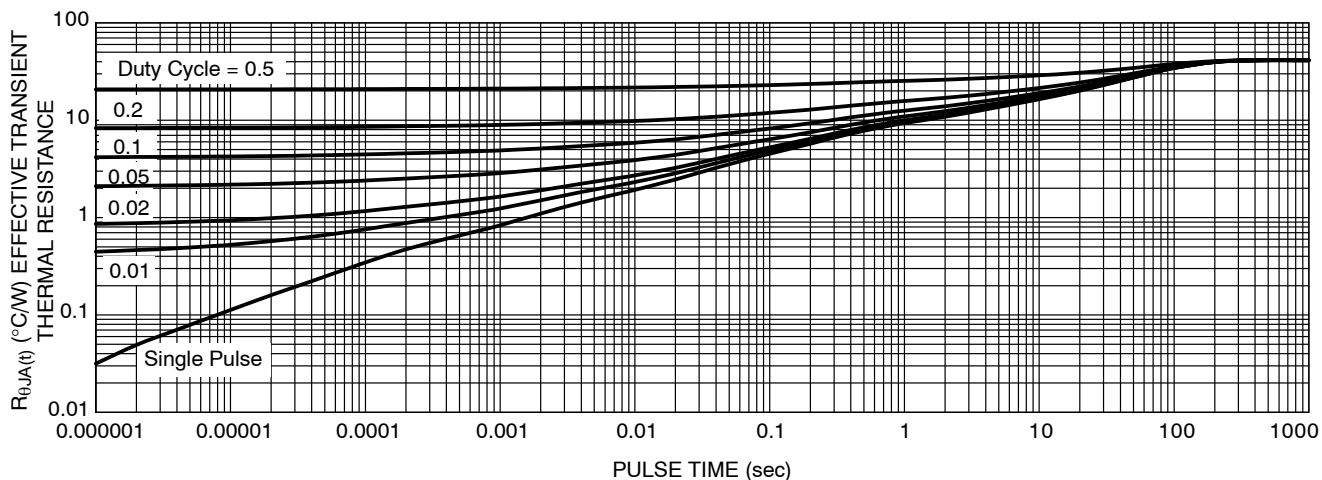


Figure 12. Thermal Response

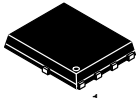
DEVICE ORDERING INFORMATION

| Device | Marking | Package | Shipping† |
|------------------|---------|-------------------|--------------------|
| NVMFS5885NLT1G | V5885L | DFN5 (Pb-Free) | 1500 / Tape & Reel |
| NVMFS5885NLWFT1G | 5885LW | DFN5 (Pb-Free) | 1500 / Tape & Reel |
| NVMFS5885NLT3G | V5885L | DFN5 (Pb-Free) | 5000 / Tape & Reel |
| NVMFS5885NLWFT3G | 5885LW | DFN5 (Pb-Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



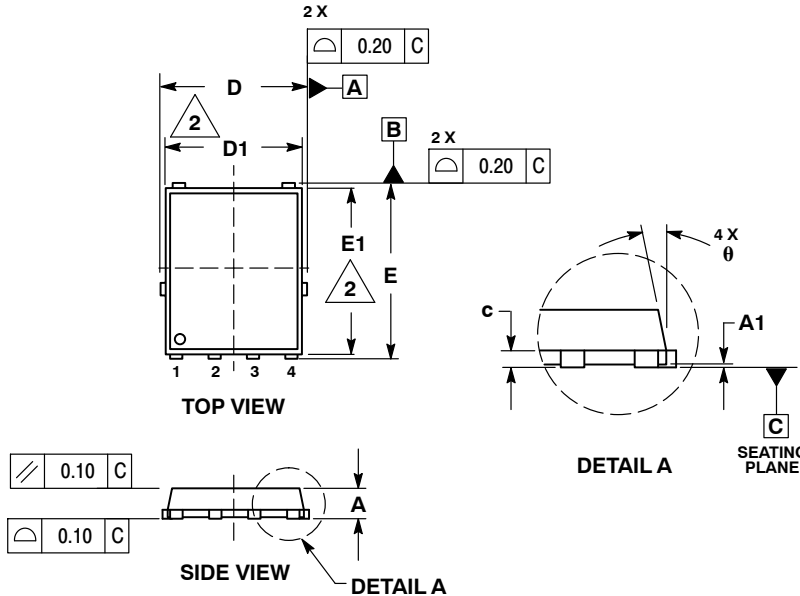
**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



1
SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

DATE 25 JUN 2018

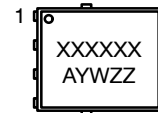


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

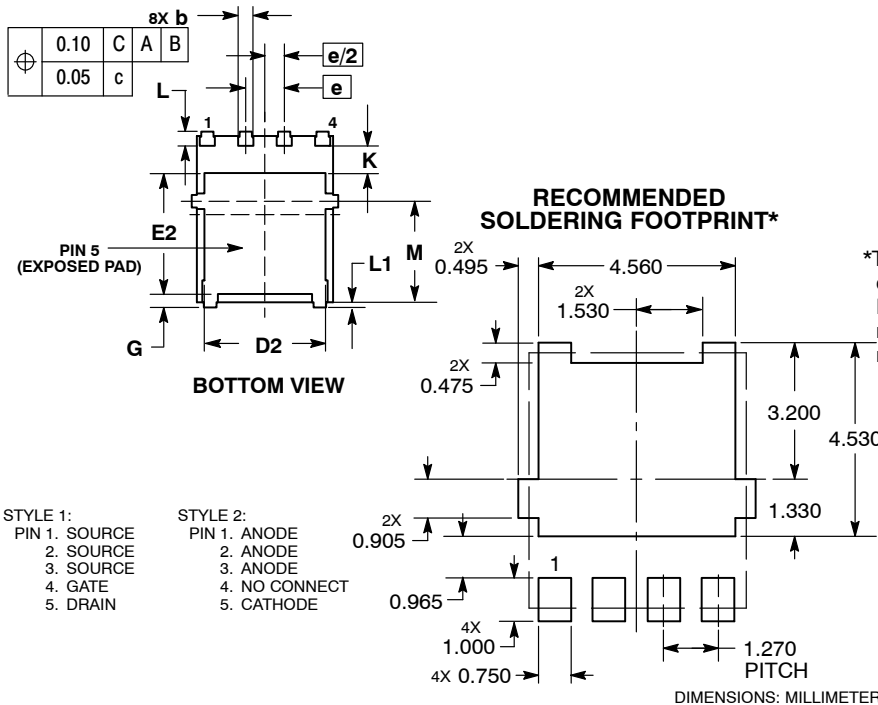
| DIM | MILLIMETERS | | |
|-------|-------------|-------|------|
| | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | --- | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.575 | 0.71 |
| K | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.575 | 0.71 |
| L1 | 0.125 REF | | |
| M | 3.00 | 3.40 | 3.80 |
| theta | 0° | --- | 12° |

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
|-------------------------|---------------------------------|--|
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| DESCRIPTION: | DFN5 5x6, 1.27P (SO-8FL) | PAGE 1 OF 1 |

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